

## ABS22 THRU ABS210 Bridge Rectifier

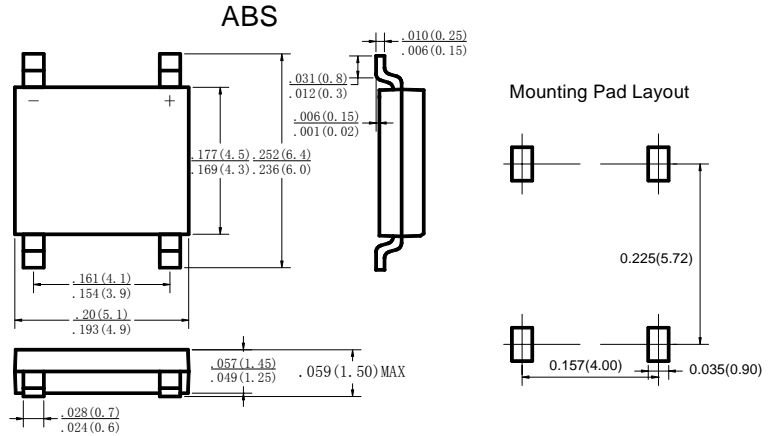
### Features

- $I_o$             2A
- $V_{RRM}$         50V~1000V
- Glass passivated chip
- High surge forward current capability

### Applications

- General purpose 1 phase Bridge rectifier applications

### Outline Dimensions and Mark



Dimensions in inches and (millimeters)

### Limiting Values (Absolute Maximum Rating)

Item	Symbol	Unit	Conditions	ABS2				
				2	4	6	8	10
Repetitive Peak Reverse Voltage	$V_{RRM}$	V		200	400	600	800	1000
Average Rectified Output Current	$I_o$	A	60Hz sine wave, R-load, $T_a=25^\circ\text{C}$	2.0				
Surge(Non-repetitive)Forward Current	$I_{FSM}$	A	60Hz sine wave, 1 cycle, $T_j=25^\circ\text{C}$	50				
Current Squared Time	$I^2t$	$\text{A}^2\text{S}$	$1\text{ms} \leq t < 8.3\text{ms}$ , $T_j=25^\circ\text{C}$ , Rating of per diode	11				
Storage Temperature	$T_{stg}$	$^\circ\text{C}$		-55 ~+150				
Junction Temperature	$T_j$	$^\circ\text{C}$		-55 ~+150				

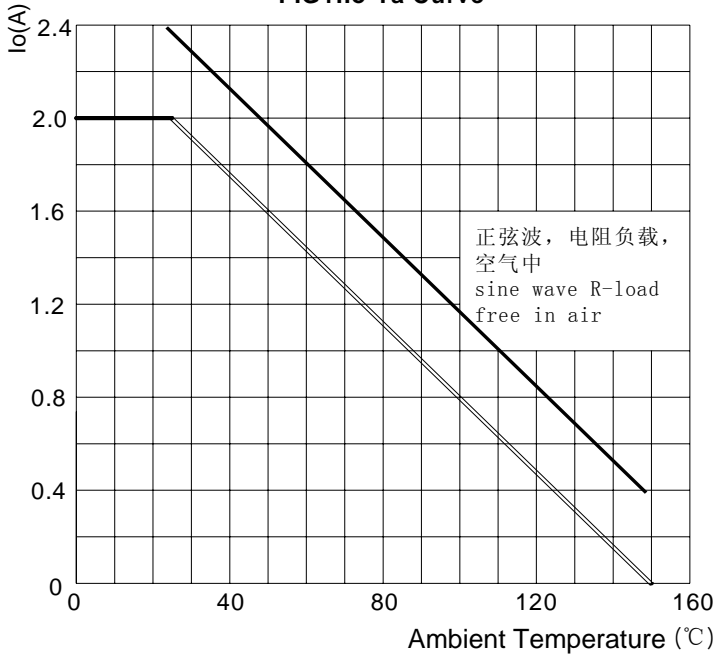
### Electrical Characteristics ( $T_a=25^\circ\text{C}$ Unless otherwise specified)

Item	Symbol	Unit	Test Condition	Max
Peak Forward Voltage	$V_{FM}$	V	$I_{FM}=1.0\text{A}$ , Pulse measurement, Rating of per diode	0.95
Peak Reverse Current	$I_{RRM}$	$\mu\text{A}$	$V_{RM}=V_{RRM}$ , Pulse measurement, Rating of per diode	10
Thermal Resistance	$R_{\theta\text{ J-A}}$	$^\circ\text{C/W}$	Between junction and ambient, On glass-epoxi substrate	62.5
	$R_{\theta\text{ J-L}}$		Between junction and lead	25

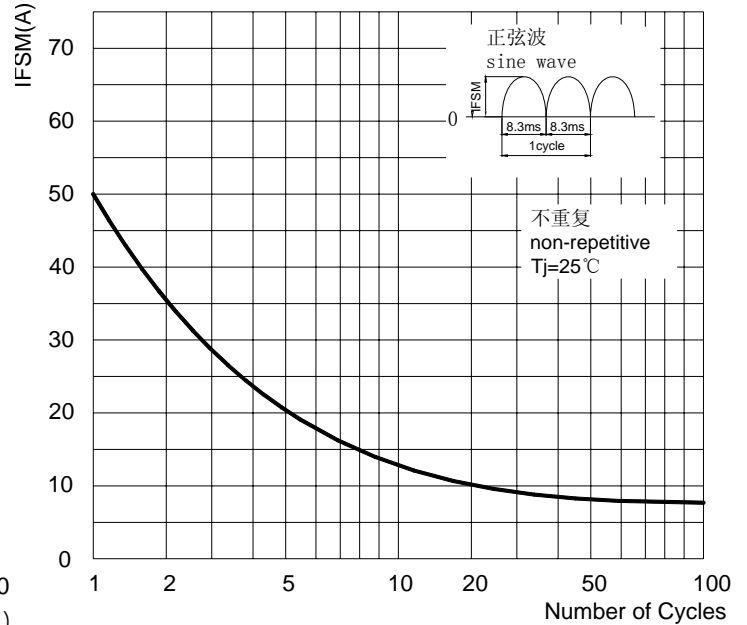
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## Characteristics(Typical)

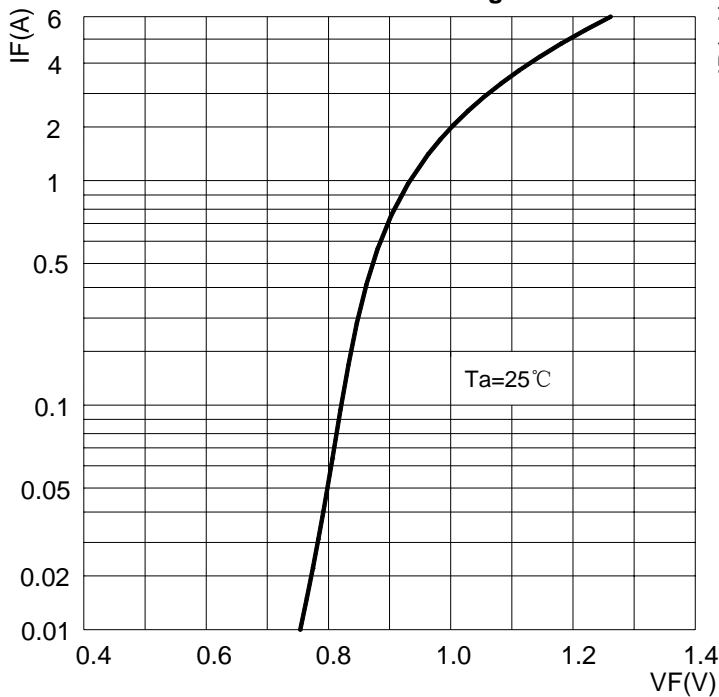
**FIG1:Io-Ta Curve**



**FIG2:Surge Forward Current Capadity**



**FIG3: Forward Voltage**



**FIG4:Typical Reverse Characteristics**

